

BEST AVAILABLE COPY**IN THE CLAIMS**

1. (Currently Amended) An etching method comprising:
providing a wafer having a dielectric layer and an electrode partially protruding from
a top surface of the dielectric layer;
etching the dielectric layer with a chemical solution; and
prior to etching the dielectric layer, reducing the protruding portion of the electrode,
wherein reducing the protruding portion includes recessing a top surface of the electrode at
least 500 angstroms below the top surface of the dielectric layer.
2. (Original) The method of claim 1, wherein the protruding portion of the
electrode is reduced sufficiently to prevent any bubbles included in the chemical solution
from adhering to the electrode.
- 3-6. (Canceled)
7. (Original) The method of claim 1, wherein reducing the protruding portion
comprises dry etching.
8. (Original) The method of claim 7, wherein drying etching uses an etchant
selected from the group consisting of HB₄, Cl₂, CF₄, C₄F₈, C₅F₈, SF₆, O₂ and combinations
thereof.
9. (Original) The method of claim 1, wherein reducing the protruding portion
comprises wet etching.
10. (Original) The method of claim 9, wherein wet etching uses a polysilicon
etchant.
- 11-41. (Canceled)